

# Lithium titanium oxynitride thin film with enhanced lithium storage and rate capability



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## ABSTRACT

The lithium titanium oxynitride (LTON) thin film electrode was prepared by radio frequency (RF) magnetron sputtering deposition using a cubic spinel structure  $\text{Li}_4\text{Ti}_5\text{O}_{12}$  (LTO) powder target in a  $\text{N}_2$  atmosphere for lithium ion batteries. XRD and SEM test results showed that the thin film was composed of weak crystal or amorphous structure and that its surface was homogeneous. XPS analyses indicated that nitrogen atoms were actually incorporated into the LTO matrix framework. The substitution of nitrogen for oxygen in the thin film created more abundant cross-linking structures, which favored the higher mobility of lithium ions. The LTON had a high capacity of  $290 \text{ mAh g}^{-1}$  at 0.1C, excellent rate capability of  $160 \text{ mAh g}^{-1}$  at 5C and only  $\approx 7\%$  capacity loss after 100 cycles at 5C charge and discharge rate. These properties make this thin film electrode a promising candidate material for use in thin film lithium ion batteries.

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## 1. Introduction

Rechargeable lithium ion thin film batteries (TFBs) will find a potential application as a power source in the miniaturization of electronic devices [1–4]. During the last years, lithium titanium oxide (LTO) has been prepared for thin film rechargeable lithium ion batteries. However, the rate capability of LTO is relatively low because of its poor electronic conductivity ( $<10^{-13} \text{ S cm}^{-1}$ ) and sluggish lithium ion diffusion [5,6]. The properties of LTO might not be sufficient for high current applications before any materials modifications.

It has been recently reported that the nitridation of the Ti-based compounds (LTO and  $\text{TiO}_2$ ) can form a more conductive  $\text{TiO}_x\text{N}_y$  species [7–10]. The highly conducting  $\text{TiO}_x\text{N}_y$  provide a short lithium ion diffusion length and a high electronic conductivity along the surface. Unfortunately, thin  $\text{TiO}_x\text{N}_y$  layers covered on the surface can just improve the electrical conductivity of the surface of LTO or  $\text{TiO}_2$ . There is no significant contribution to the internal mass transfer capability. If  $\text{TiO}_x\text{N}_y$  species are formed inside the

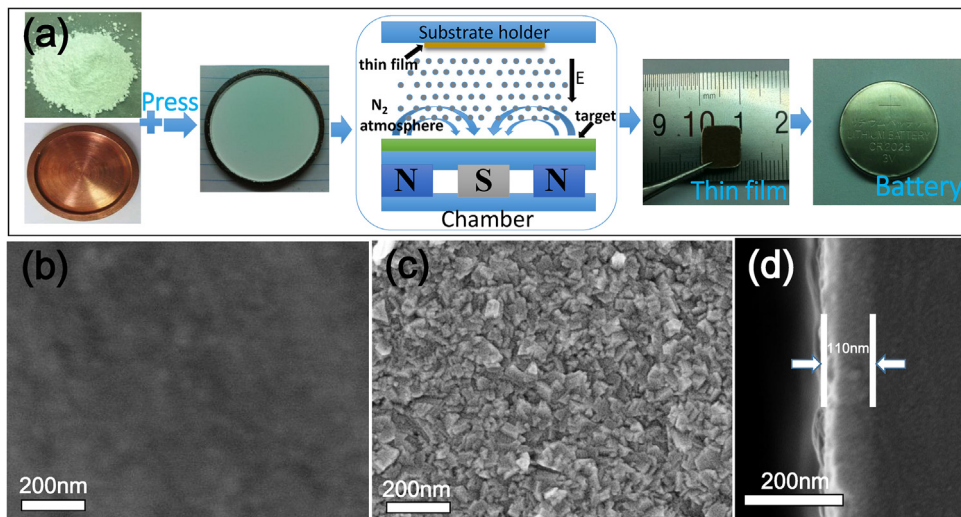
LTO thin film, it will significantly improve electronic conductivity and enhance lithium storage capacity. So in this article we report a successful preparation of amorphous LTON thin films by using RF magnetron sputtering in a  $\text{N}_2$  atmosphere with a LTO powder target.

## 2. Experimental

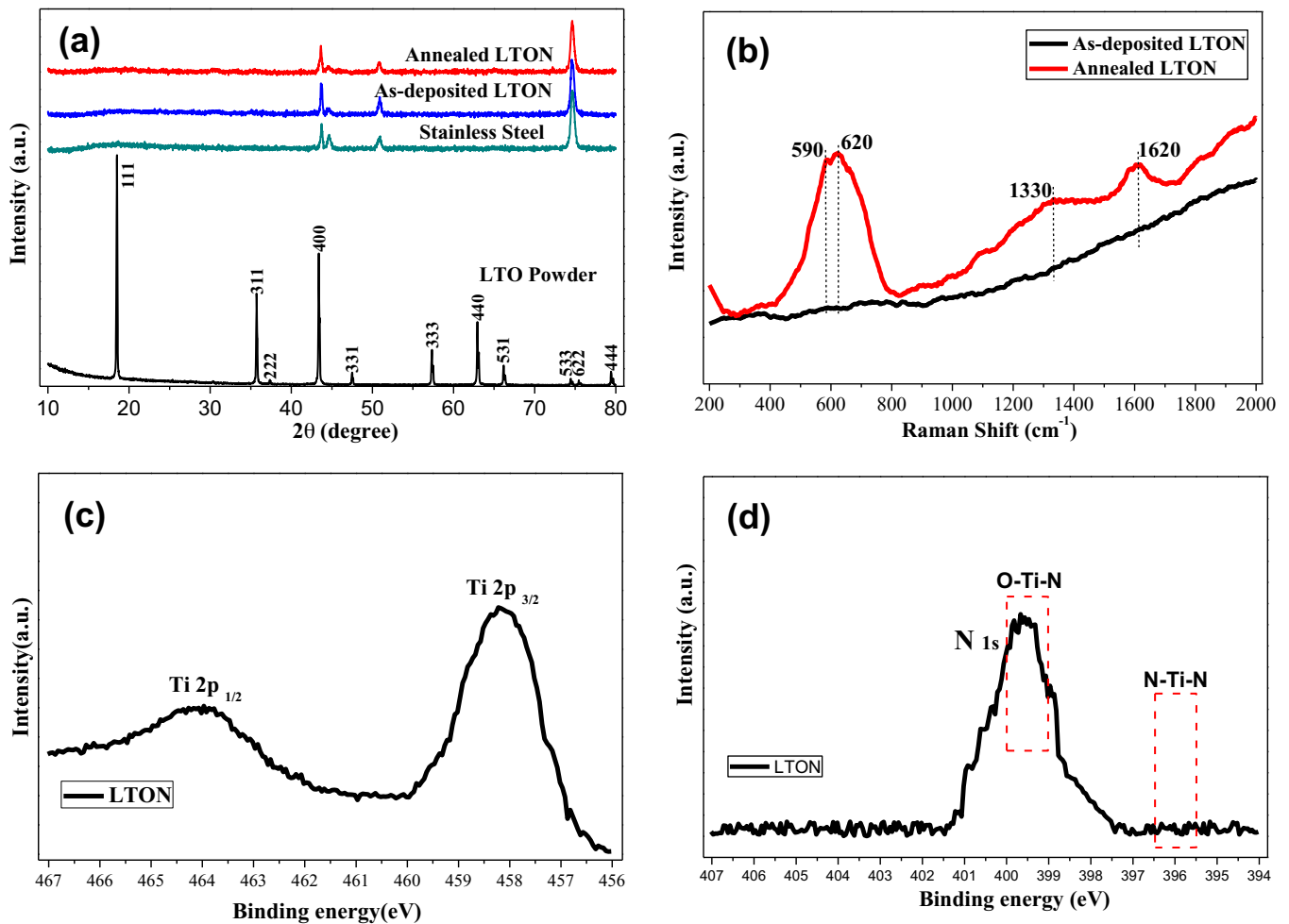
### 2.1. Preparation of electrodes

The LTO powder ( $\text{Li}_4\text{Ti}_5\text{O}_{12}$ , >99%, Btr New Energy materials INC, Shenzhen, China) was dried at  $120^\circ\text{C}$  over 10 h. The powder was pressed into a copper target holder (70 mm in diameter) with 5 ton uniaxial presses. No further processes were involved in powder target production. The LTON thin film electrodes were deposited onto a stainless steel (SS) substrate using JPG-560C12 (SKY Technology Development Limited Company of Chinese Academy of Sciences, Shenyang, China) RF magnetron sputtering system. The SS substrate-target distance was 70 mm. The substrate was held at  $400^\circ\text{C}$  during the deposition. LTON thin film with a thickness of 110 nm was prepared by sputtering for 2 h at an applied power of 80 W in a high-purity  $\text{N}_2$  atmosphere of  $1.6 \times 10^{-2}$  mbar pressure. Films were annealed after deposition in flowing Ar at  $700^\circ\text{C}$  for 2 h. The film electrode mass are measured by high precision analytical balance.

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**Fig. 1.** (a) Schematic illustration for the fabrication of LTON. (b) and (c) SEM images of as-deposited LTON and annealed LTON. (d) Cross-sectional SEM images of LTON.



**Fig. 2.** (a) XRD pattern of Powder target, SS, as-deposited and annealed LTON thin films. (b) Raman spectra of as-deposited and annealed LTON thin films. (c) and (d) Overlay of normalized Ti<sub>2p</sub> and N<sub>1s</sub> core level XPS spectra of LTON.

## 2.2. Characterization of materials

The crystal structure of the obtained samples was characterized by X-ray diffraction (XRD, Rigaku DMAX 2500, Tokyo, Japan) using Cu K $\alpha$  radiation, Raman spectra (JY Labram HR 800) and

X-ray photoelectron spectroscopy (XPS, thermo ESCALAB 250Xi spectrometer) using Al K $\alpha$  (at 1486.6 eV) as the X-ray source. The microstructural properties were characterized using scanning electron microscopy (SEM) (SEM, Hitachi S-4800, Tokyo, Japan).

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